

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±10	V
Continuous Drain Current, V _{GS} = -4.5V (Note 7)	T _C = +25°C T _C = +70°C	ID	-50 -40	A
Maximum Continuous Body Diode Forward Current (Note 7)	ls	-50	А	
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)		I _{DM}	-80	А
Avalanche Current, L = 0.1mH (Note 8)		I _{AS}	-35	A
Avalanche Energy, L = 0.1mH (Note 8)		E _{AS}	64	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	1.0	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ extsf{ heta}JA}$	122	°C/W	
Total Power Dissipation (Note 6)		PD	2.0	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ hetaJA}$	62	°C/W	
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	3.5	C/VV		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	—	-1	μA	V _{DS} = -16V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-0.4	—	-1.2	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance		—	7.5	9.5	mΩ	V _{GS} = -4.5V, I _D = -3.6A	
Static Drain-Source On-Resistance	R _{DS(ON)}	—	9.5	12.5		V _{GS} = -2.5V, I _D = -3.6A	
Diode Forward Voltage	V _{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -10A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	—	3350	_		V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss	—	527	_	pF		
Reverse Transfer Capacitance	Crss	—	460	—			
Gate Resistance	R _G	_	10.7	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	50	—			
Total Gate Charge (V _{GS} = -10V)	Qg	_	103	_	nC	$V_{DS} = -10V, I_D = -3.6A$	
Gate-Source Charge	Q _{gs}	_	6.0	_	nc		
Gate-Drain Charge	Q _{gd}	_	14.4	_			
Turn-On Delay Time	t _{D(ON)}	_	9.7	_			
Turn-On Rise Time	t _R	_	30	_		V_{DD} = -10V, V_{GS} = -4.5V, R _{GEN} = 4.7 Ω , I _D = -3.6A	
Turn-Off Delay Time	t _{D(OFF)}	_	235	_	ns		
Turn-Off Fall Time	t _F	_	110	_	1		
Reverse Recovery Time	t _{RR}	_	64	—	ns	I _F = -3.6A, di/dt = 100A/μs	
Reverse Recovery Charge	Q _{RR}	—	60	—	nC		

Notes:

Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).

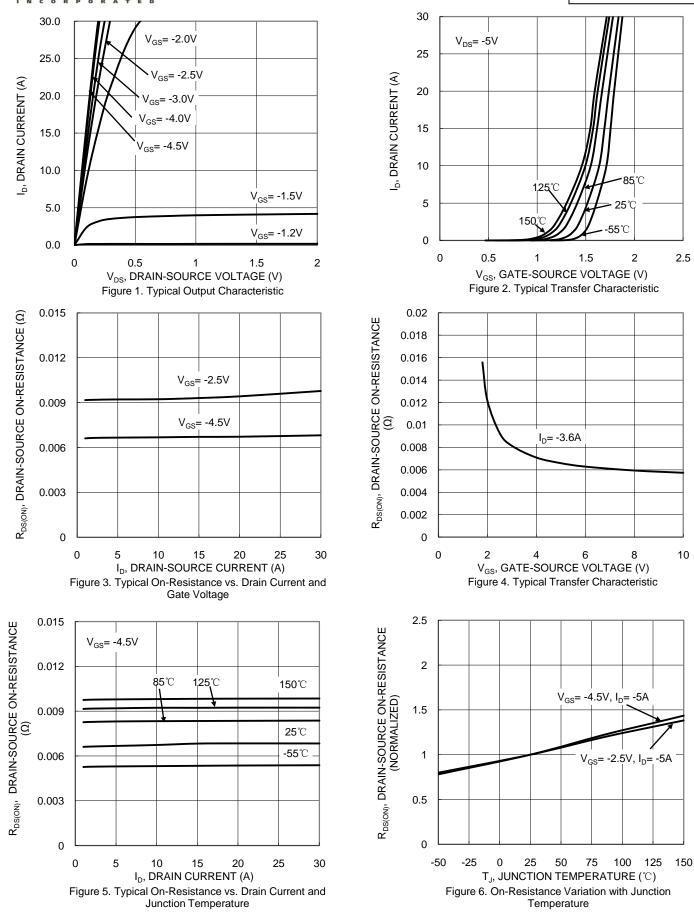
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.



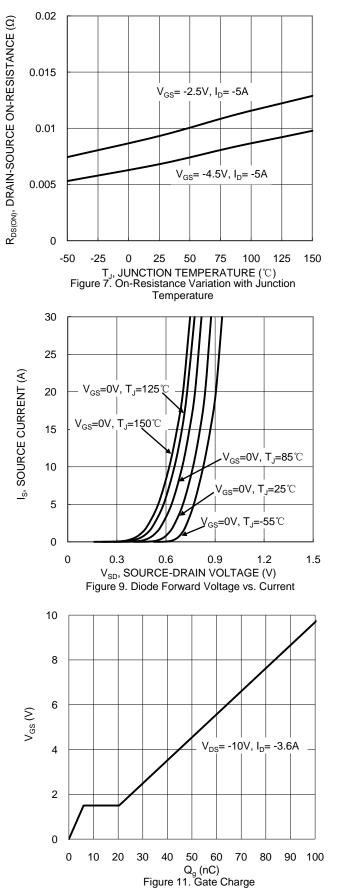


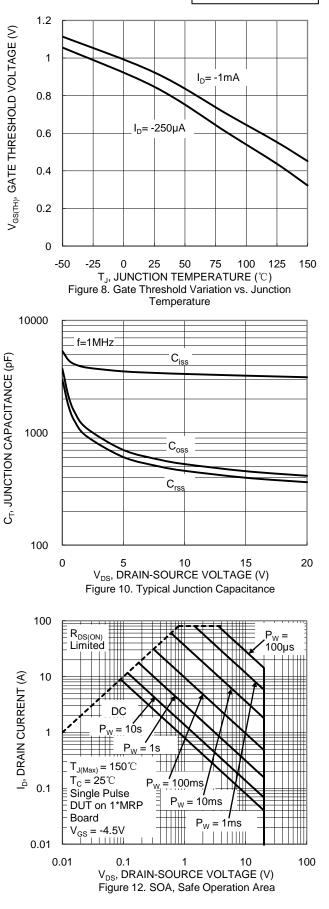


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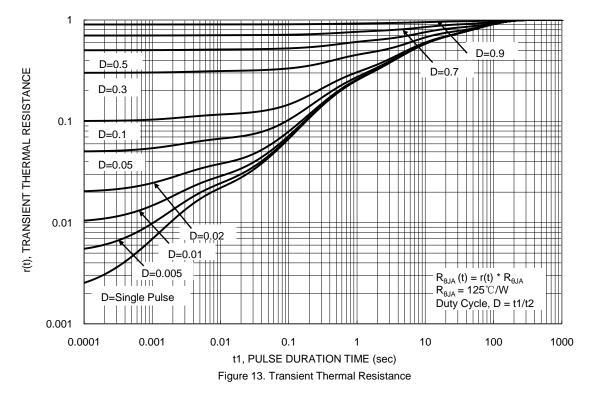






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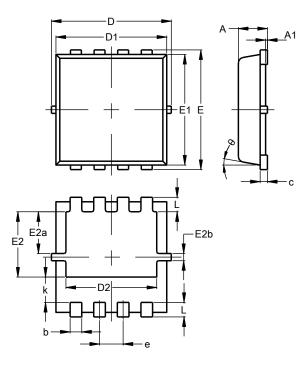




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

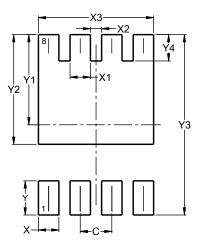


PowerDI3333-8 (Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
c	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
ш	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
e	0.65 BSC				
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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